

1N483B THRU 1N486B SERIES
LOW POWER MINIATURE GLASS PASSIVATED SILICON DIODES

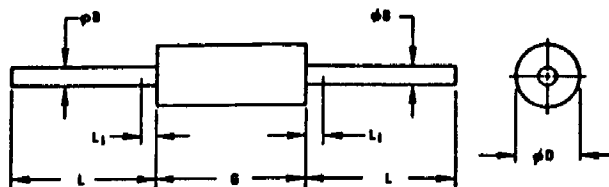
FEATURES:

- High temperature metallurgically bonded
- 0.2 amperes operation at $T_A = 25^\circ\text{C}$ with no thermal runaway
- Hermetically sealed package
- Ideally suited for miniaturized equipment
- Glass passivated cavity-free junction

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS				
Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.				
	1N483B	1N485B	1N486B	Units
* Maximum Recurrent Peak Reverse Voltage	70	180	225	V_{RRM}
Maximum RMS Voltage	50	127	159	V_{RMS}
* Maximum DC Blocking Voltage	70	180	225	V_{DC}
* Maximum Reverse Breakdown Voltage at 100 μA	80	200	250	V_{PK}
* Maximum Average Forward Rectified Current $T_A = 25^\circ\text{C}$.375" (9.5mm) Lead Length at $T_A = 150^\circ\text{C}$		200 50		mA(AV) mA(AV)
* Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		2.0		Apk
* Maximum Instantaneous Forward Voltage at 100mA		1.0		V_{PK}
* Maximum DC Reverse Current at Rated DC Blocking Voltage		25 5.0		NA μA
Typical Junction Capacitance (Note 1)		15		pF
* Operating and Storage Temperature Range T_J, T_{STG}		-65 to +200		$^\circ\text{C}$

NOTES:
 1. Measured at 1.0MHz and applied reverse voltage of 4.0VDC.
 2. Available to JAN and JANTX Military Specifications MIL-8-19600/116C
 * JEDEC Registered Value.

D0-7



SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
ϕB	.018	.022	0.458	0.558	-
ϕD	.085	.107	2.16	2.71	1
G	.230	.300	5.85	7.62	1
L	1.000	-	25.40	-	-
L_1	-	.050	-	1.27	2

NOTES:

1. PACKAGE CONTOUR OPTIONAL WITHIN CYLINDER OF DIAMETER ϕD AND LENGTH G. SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER BUT SHALL NOT BE SUBJECT TO THE MINIMUM LIMIT OF ϕD
2. LEAD DIAMETER NOT CONTROLLED IN THIS ZONE TO ALLOW FOR FLASH LEAD FINISH BUILD-UP, AND MINOR IRREGULARITIES OTHER THAN SLUGS.

